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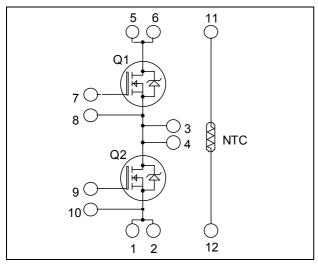


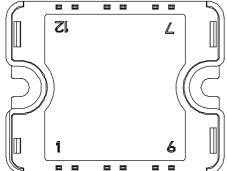




Phase leg MOSFET Power Module

$$\begin{split} V_{DSS} &= 1000V \\ R_{DSon} &= 400 m \Omega \text{ typ @ Tj} = 25^{\circ} C \\ I_D &= 21A \text{ @ Tc} = 25^{\circ} C \end{split}$$





Pins 1/2; 3/4; 5/6 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 8TM Fast FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		1000	V
Ţ	Continuous Drain Current	$T_c = 25^{\circ}C$	21	
I_D	Continuous Drain Current	$T_c = 80$ °C	16	A
I_{DM}	Pulsed Drain current		140	
V_{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		480	mΩ
P_{D}	Maximum Power Dissipation	$T_c = 25$ °C	390	W
I_{AR}	Avalanche current (repetitive and non repetitive)		18	A

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25^{\circ}$ C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
ī	Zero Gate Voltage Drain Current	$V_{DS} = 1000V$	$T_j = 25$ °C			250	^
I_{DSS}		$V_{GS} = 0V$	$T_j = 125$ °C			1000	μΑ
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 18A$			400	480	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 2.5 \text{mA}$		3	4	5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}$				±100	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		7868		
C_{oss}	Output Capacitance	$V_{\rm DS} = 25V$		825		pF
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		104		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		305		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 500V$		55		nC
Q_{gd}	Gate – Drain Charge	$I_{D} = 18A$		145		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C		44		
$T_{\rm r}$	Rise Time	$\begin{aligned} V_{GS} &= 15V \\ V_{Bus} &= 667V \\ I_D &= 18A \end{aligned}$		40		
$T_{d(off)}$	Turn-off Delay Time			150		ns
T_{f}	Fall Time	$R_G = 2.2\Omega$		38		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_S	Continuous Source current		$Tc = 25^{\circ}C$			21	Α
	(Body diode)		$Tc = 80^{\circ}C$			16	Λ
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -18A$	\			1.1	V
dv/dt	Peak Diode Recovery					25	V/ns
+	Reverse Recovery Time		$T_j = 25^{\circ}C$			300	200
t_{rr}	Reverse Recovery Time	$I_S = -18A$ $V_R = 100V$	$T_j = 125$ °C			650	ns
0	Reverse Recovery Charge	$di_{S}/dt = 100 \text{ A}/\mu\text{s}$	$T_j = 25$ °C		1.61		μС
Q_{rr}	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		4.21		μС

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq \text{--} 16A \qquad di/dt \leq 1000 A/\mu s \qquad V_{DD} \leq 667 V \qquad T_j \leq 125 ^{\circ} C$



Thermal and package characteristics

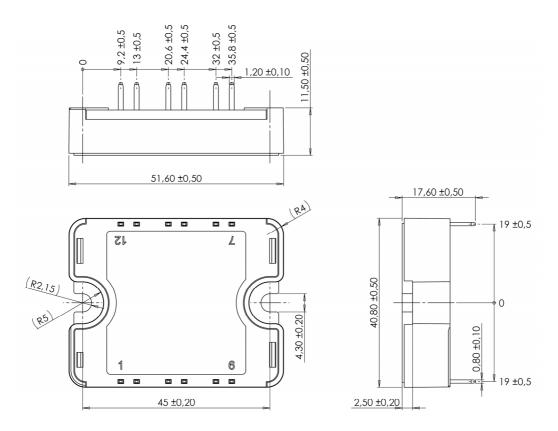
Symbol	Characteristic		Min	Тур	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance				0.32	°C/W	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V	
T_{J}	Operating junction temperature range		-40		150		
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight				80	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature at T

SP1 Package outline (dimensions in mm)

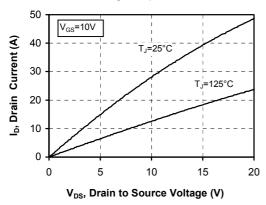


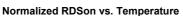
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

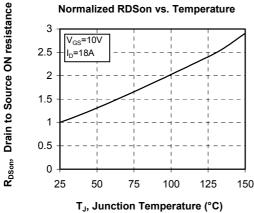


Typical Performance Curve

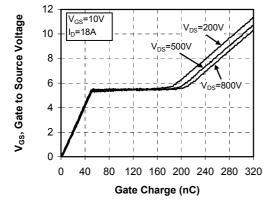
Low Voltage Output Characteristics



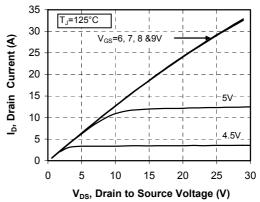




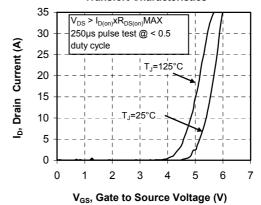
Gate Charge vs Gate to Source



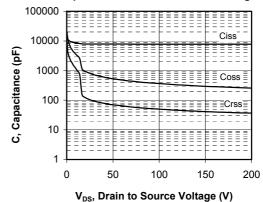
Low Voltage Output Characteristics



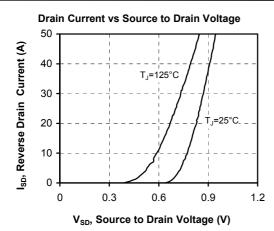
Transfert Characteristics

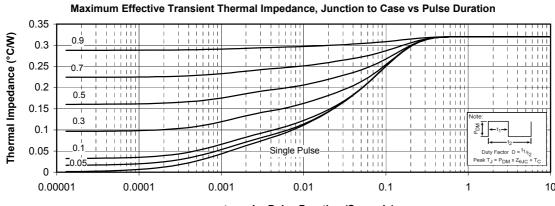


Capacitance vs Drain to Source Voltage









5 - 6

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